

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HVU132

Silicon Epitaxial Planar Pin Diode for High Frequency Switching



ADE-208-321B(Z)

Rev. 2
Feb. 2000

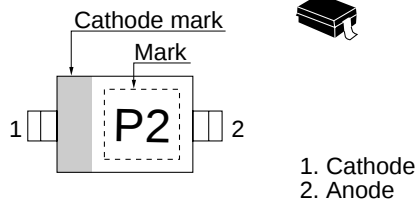
Features

- Low capacitance. ($C=0.5\text{pF}$ max)
- Low forward resistance. ($r_f=2.0\Omega$ max)
- Ultra small Resin Package (URP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HVU132	P2	URP

Outline



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	65	V
Reverse voltage	V_R	60	V
Forward current	I_F	100	mA
Power dissipation	P_d	150	mW
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	I_R	—	—	0.1	μ A	$V_R = 60V$
Forward voltage	V_F	—	—	1.0	V	$I_F = 10\text{ mA}$
Capacitance	C	—	—	0.5	pF	$V_R = 1V, f = 1\text{ MHz}$
Forward resistance	r_f	—	—	2.0	Ω	$I_F = 10\text{ mA}, f = 100\text{ MHz}$

Main Characteristic

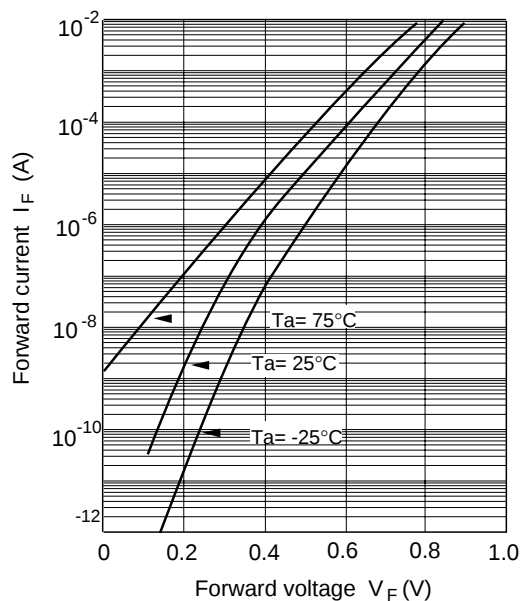


Fig.1 Forward current Vs. Forward voltage

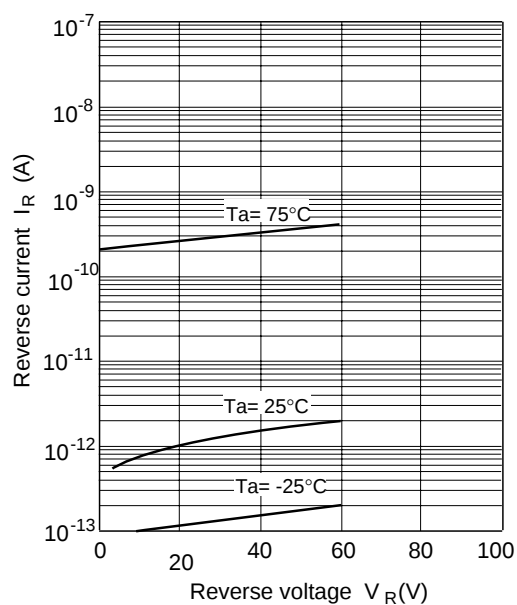


Fig.2 Reverse current Vs. Reverse voltage

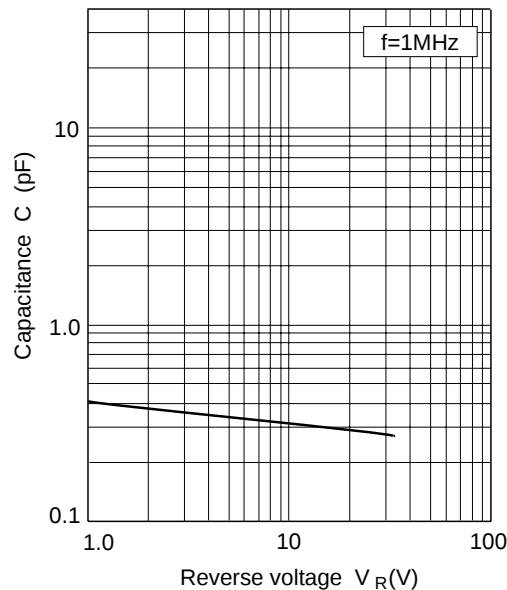


Fig.3 Capacitance Vs. Reverse voltage

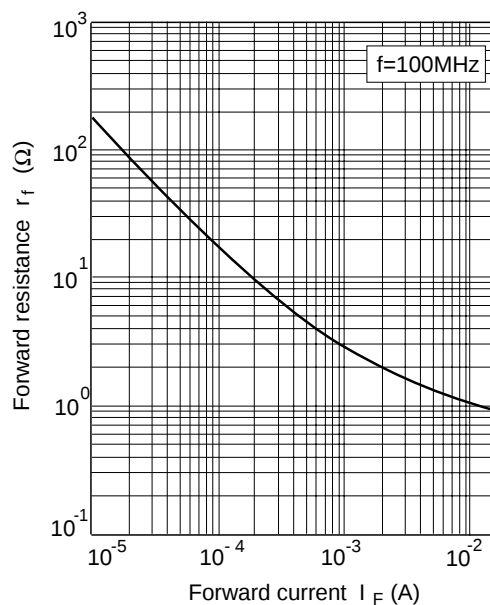
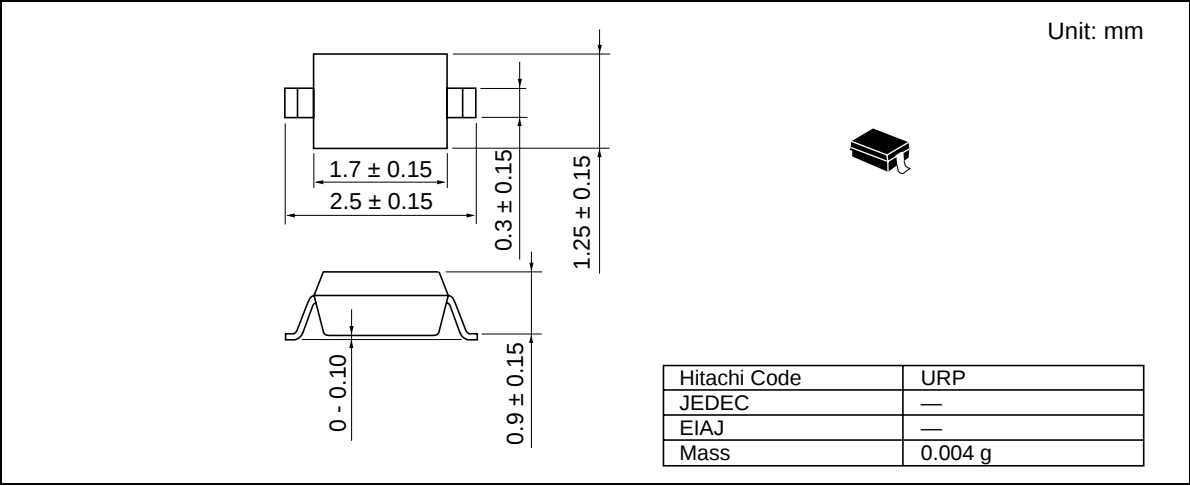


Fig.4 Forward resistance Vs. Forward current

Package Dimensions



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